

2SC4656

Silicon NPN epitaxial planer type

For high-frequency amplification

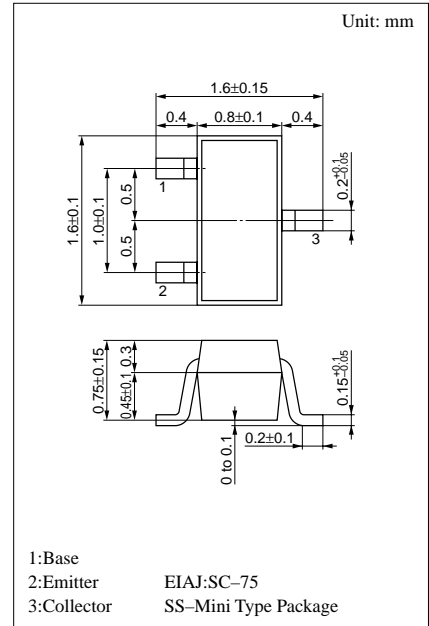
Complementary to 2SA1791

■ Features

- Small collector output capacitance C_{ob} .
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	50	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 ~ +125	°C



Marking symbol : AM

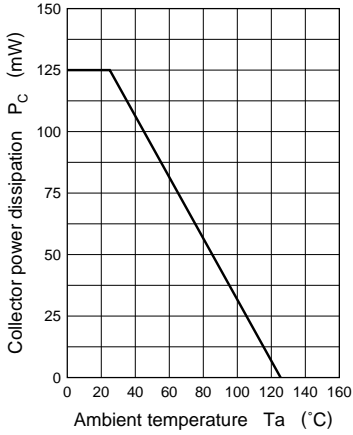
■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 10V, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 10V, I_B = 0$			100	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	50			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	50			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 10V, I_C = 2mA$	200		500	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.06	0.3	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		250		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		1.5		pF

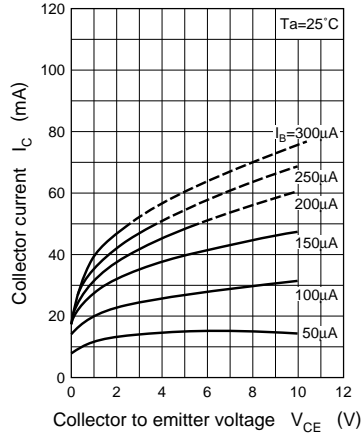
* h_{FE} Rank classification

Rank	Q	R
h_{FE}	200 ~ 400	250 ~ 500
Marking Symbol	AMQ	AMR

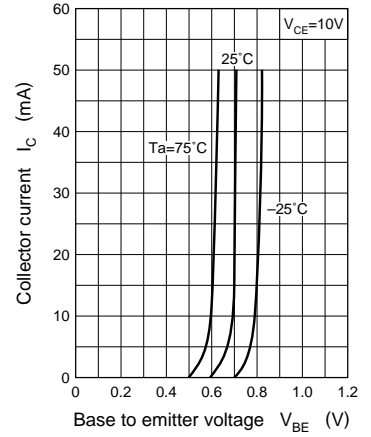
$P_C - T_a$



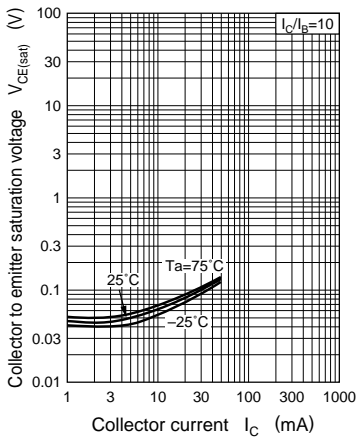
$I_C - V_{CE}$



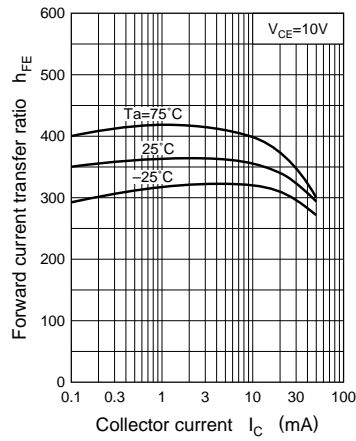
$I_C - V_{BE}$



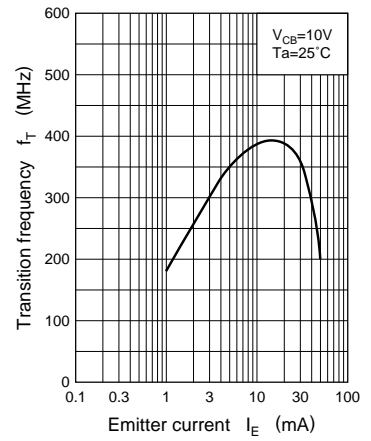
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

